

2SA1323

Silicon PNP epitaxial planer type

For high-frequency amplification

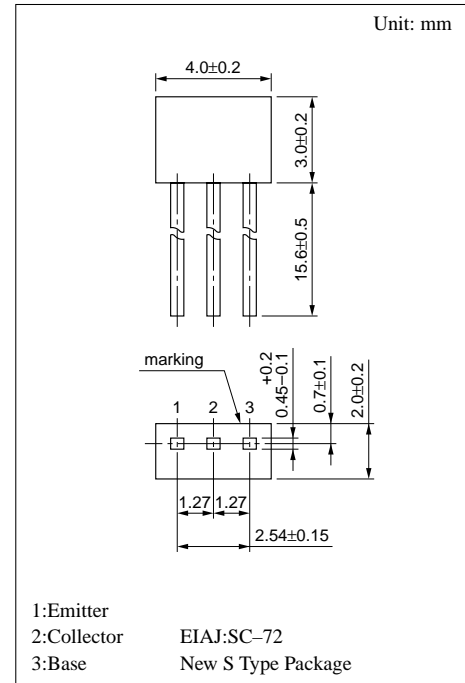
Complementary to 2SC3314

■ Features

- Allowing supply with the radial taping.
- High transition frequency f_T .
- Optimum for high-density mounting.

■ Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-30	V
Collector to emitter voltage	V_{CEO}	-20	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-60	mA
Collector current	I_{C}	-30	mA
Collector power dissipation	P_{C}	300	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$



■ Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{\text{CB}} = -10\text{V}, I_{\text{E}} = 0$			-0.1	μA
	I_{CEO}	$V_{\text{CE}} = -20\text{V}, I_{\text{B}} = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{\text{EB}} = -5\text{V}, I_{\text{C}} = 0$			-10	μA
Forward current transfer ratio	h_{FE}^*	$V_{\text{CE}} = -10\text{V}, I_{\text{C}} = -1\text{mA}$	70		220	
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10\text{mA}, I_{\text{B}} = -1\text{mA}$		-0.1		V
Base to emitter voltage	V_{BE}	$V_{\text{CE}} = -10\text{V}, I_{\text{C}} = -1\text{mA}$		-0.7		V
Transition frequency	f_T	$V_{\text{CB}} = -10\text{V}, I_{\text{E}} = 1\text{mA}, f = 200\text{MHz}$	150	300		MHz
Noise figure	NF	$V_{\text{CB}} = -10\text{V}, I_{\text{E}} = 1\text{mA}, f = 5\text{MHz}$		2.8	4.0	dB
Reverse transfer impedance	Z_{rb}	$V_{\text{CB}} = -10\text{V}, I_{\text{E}} = 1\text{mA}, f = 2\text{MHz}$		22	50	Ω
Common emitter reverse transfer capacitance	C_{re}	$V_{\text{CE}} = -10\text{V}, I_{\text{C}} = -1\text{mA}, f = 10.7\text{MHz}$		1.2	2.0	pF

* h_{FE} Rank classification

Rank	B	C
h_{FE}	70 ~ 140	110 ~ 220

